	3	[an RPID] a radio frequency transceiver circuit [and a battery] mounted between the two	
	6	covers;	
	7	wherein the two covers are sealed together along a peripheral contour which completely	
	8	encircles the transceiver [and battery].	
		.1	
	ي ۋ	26 (amended) A transceiver according to claim 25, wherein the barrier material is a substance select	ted
7	LZ	from the set consisting of silicon oxide and silicon nitride.	
\mathcal{D})	.1	
	1 =	3 27 (amended) A transceiver according to claim 25, wherein the barrier material is a substance select	ted
~	2	from the set consisting of polyethylene and polyvinylidenechloride (PVDC).	
_	-,-	from the sea-consisting of polychrytene and polyvinyhdeneemonde (1 vDC).	
	, (1 (amended) A method of manufacturing a radio frequency (identification (PEID)) transcriver	
	'n	1. 42. (amended) A method of manufacturing a radio frequency [identification (RFID)] transceiver,	
	2	comprising the steps of:	
2	3 ر	providing two covers, each cover being composed of a sheet of polymer film;	
)	4	forming on each of the two covers a barrier material which is a barrier to water vapor;	
	5	mounting [an RFID] a transceiver circuit [and a battery] between the two covers; and	
	6	sealing the two covers together along a peripheral contour which completely encircles the	
	7	transceiver [and battery].	
	•	transcerver fand battery.	
_		transcerver [and battery].	
		Insert the following new claims 43–50:	 -
- 5	11		WP *
5	1 1 2	Insert the following new claims 43–50:	WP **
5	1 / 2	Insert the following new claims 43–50: O. 43. A method according to claim 42, wherein the barrier material is a substance selected from the set	WP 10
_/ 	1 / 2	Insert the following new claims 43–50: 37-04 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride.	P
_/	1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. Show the set of t	サナーサナ
_/ 5	1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC).	サナーサナ
_/ 5	1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC).	サケーサケ
_/ 5	1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC).	'\
_/ 5	1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC).	'\
-/ 5	1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC). 45. A method according to claim 42, wherein the barrier material is perchlorotetrafluoroethylene.	'\
-/ 5 3	1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC). 45. A method according to claim 42, wherein the barrier material is perchlorotetrafluoroethylene. 46. A method according to claim 42, wherein the forming step comprises forming the barrier material as a layer having a thickness of 400 to 10,000 angstroms.	'\
_/ 5 .3	1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC). 45. A method according to claim 42, wherein the barrier material is perchlorotetrafluoroethylene. 46. A method according to claim 42, wherein the forming step comprises forming the barrier material as a layer having a thickness of 400 to 10,000 angstroms.	'\
_/ 5	1 / 2 1 / 2 1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC). 45. A method according to claim 42, wherein the barrier material is perchlorotetrafluoroethylene. 46. A method according to claim 42, wherein the forming step comprises forming the barrier material as a layer having a thickness of 400 to 10,000 angstroms.	' \
	1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC). 45. A method according to claim 42, wherein the barrier material is perchlorotetrafluoroethylene. 46. A method according to claim 42, wherein the forming step comprises forming the barrier material as a layer having a thickness of 400 to 10,000 angstroms.	' \
<u>/</u> / 5	1 / 2 1 / 2 1 / 2 1 / 2 1 / 2	Insert the following new claims 43–50: 43. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of silicon oxide and silicon nitride. 44. A method according to claim 42, wherein the barrier material is a substance selected from the set consisting of polyethylene and polyvinylidenechloride (PVDC). 45. A method according to claim 42, wherein the barrier material is perchlorotetrafluoroethylene. 46. A method according to claim 42, wherein the forming step comprises forming the barrier material as a layer having a thickness of 400 to 10,000 angstroms.	' \



angstroms.

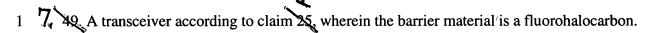
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48. A transceiver according to claim 25, wherein:

the barrier material of the first cover is an electrically conductive material;

the polymer film of the first cover is a dielectric material and is positioned between the barrier material of the first cover and the radio frequency transceiver circuit; and

the radio frequency transceiver circuit further comprises an antenna coupling circuit for capacitively coupling the transceiver circuit to the electrically conductive outer layer through the dielectric polymer film of the first cover so that the electrically conductive barrier material of the first cover functions as an antenna for the radio frequency transceiver circuit.



1 8.50. A transceiver according to claim 25, wherein the barrier material is perchlorotetrafluoroethylene.

REMARKS

Claims 25-39 and 42-50 are now pending.

Error in Correspondence Address

The PTO mailed the filing receipt to the wrong address. Please ensure that all future correspondence is addressed to the undersigned attorney of record, as specified on page 2 of the original "Request for Filing a Divisional Patent Application" filed 7/14/98, and as specified in the Power of Attorney filed 4/6/95 in parent application SN 08/137,677, a copy of which was enclosed with the request for filing the present divisional application.

Corrections to Figure 12

The drawing reference numerals in Figure 12 are inconsistent with those in the specification and Figure 11. Specifically, the numerals 270, 274, 282, 286, 290, and 294 appearing in Figure 12 do not appear anywhere in the specification or in Figure 11. Since Figure 12 is identified as a sectional view taken from Figure 11, the reference numerals in those two figures should be consistent. Therefore, Applicant requests the Examiner's approval of the changes marked in red in on the attached copy of Figures 11 and 12. The changes to the reference numerals in Figure 12 are supported by Figure 11 and by the description of Figure 12 at page 27, line 16 – page 28, line 7 of the specification.



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